imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized applications, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an equif prese

ON Semiconductor®

FDMD8440L Dual N-Channel PowerTrench[®] MOSFET

FDMD8440L Dual N-Channel PowerTrench[®] MOSFET 40 V, 87 A, 2.6 mΩ

Features

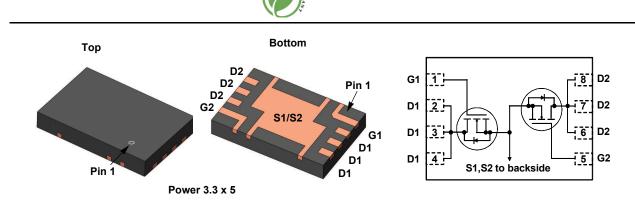
- Max r_{DS(on)} = 2.6 mΩ at V_{GS} = 10 V, I_D = 21 A
- Max r_{DS(on)} = 3.8 mΩ at V_{GS} = 4.5 V, I_D = 17 A
- Ideal for Flexible Layout in Secondary Side Synchronous Rectification
- 100% UIL Tested
- Termination is Lead-free and RoHS Compliant

General Description

This package integrates two N-Channel devices connected internally in common-source configuration. This enables very low package parasitics and optimized thermal path to the common source pad on the bottom. It provides a very small footprint $(3.3 \times 5 \text{ mm})$ for higher power density.

Applications

- Isolated DC-DC Synchronous Rectifiers
- Common Ground Load Switches



MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted.

Symbol	Param	eter		Ratings	Units	
V _{DS}	Drain to Source Voltage			40	V	
V _{GS}	Gate to Source Voltage			±20	V	
	Drain Current -Continuous	T _C = 25 °C	(Note 5)	87		
	-Continuous	T _C = 100 °C	(Note 5)	55	•	
D	-Continuous	T _A = 25 °C	(Note 1a)	21	Α	
	-Pulsed		(Note 4)	521		
E _{AS}	Single Pulse Avalanche Energy		(Note 3)	265	mJ	
	Power Dissipation	T _C = 25 °C		33	W	
P _D	Power Dissipation	T _A = 25 °C	(Note 1a)	2.1		
T _J , T _{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C	

Thermal Characteristics

$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case	3.8	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient (Note	a) 60	C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMD8440L	FDMD8440L	Power 3.3 x 5	13 "	12 mm	3000 units

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Char	acteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0 V	40			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I_D = 250 µA, referenced to 25 °C		22		mV/°C
IDSS	Zero Gate Voltage Drain Current	V _{DS} = 32 V, V _{GS} = 0 V			1	μA
I _{GSS}	Gate to Source Leakage Current	V _{GS} = ±20 V, V _{DS} = 0 V			±100	nA
On Char	acteristics					
V _{GS(th)}	Gate to Source Threshold Voltage	V _{GS} = V _{DS} , I _D = 250 μA	1.0	1.7	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu$ A, referenced to 25 °C		-6		mV/°C
r _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 21 A		1.8	2.6	
		V _{GS} = 4.5 V, I _D = 17 A		2.6	3.8	mΩ
		V _{GS} = 10 V, I _D = 21 A, T _J = 125 °C		2.8	4.1	
9 _{FS}	Forward Transconductance	V _{DD} = 5 V, I _D = 21 A		111		S
Dynamic	Characteristics					
C _{iss}	Input Capacitance			2965	4150	pF
C _{oss}	Output Capacitance	V _{DS} = 20 V, V _{GS} = 0 V f = 1 MHz		875	1225	pF
C _{rss}	Reverse Transfer Capacitance			40	70	pF
R _g	Gate Resistance		0.1	1.6	3.2	Ω
	g Characteristics					
t _{d(on)}	Turn-On Delay Time			12	21	ns
t _r	Rise Time	V _{DD} = 20 V, I _D = 21 A		7	14	ns
t _{d(off)}	Turn-Off Delay Time	V _{GS} = 10 V, R _{GEN} = 6 Ω		34	54	ns
t _f	Fall Time			7	14	ns
Q _{g(TOT)}	Total Gate Charge	$V_{GS} = 0 V$ to 10 V		44	62	nC
	Total Gate Charge	$V_{GS} = 0 V \text{ to } 4.5 V V_{DD} = 20 V$		21	35	nC
Q _{gs}	Gate to Source Charge	I _D = 21 A		9		nC
Q _{gd}	Gate to Drain "Miller" Charge			7		nC

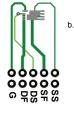
V _{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0 V, I_S = 21 A$ (Note 2)		0.8	1.2	V
t _{rr}	Reverse Recovery Time	-I _F = 21 A, di/dt = 100 A/μs		41	66	ns
Q _{rr}	Reverse Recovery Charge	$I_F = 21 \text{ A}, \text{ di/dt} = 100 \text{ A/} \mu \text{s}$		22	35	nC

NOTES:

1. R_{BLA} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{BJC} is guaranteed by design while R_{BCA} is determined by the user's board design.



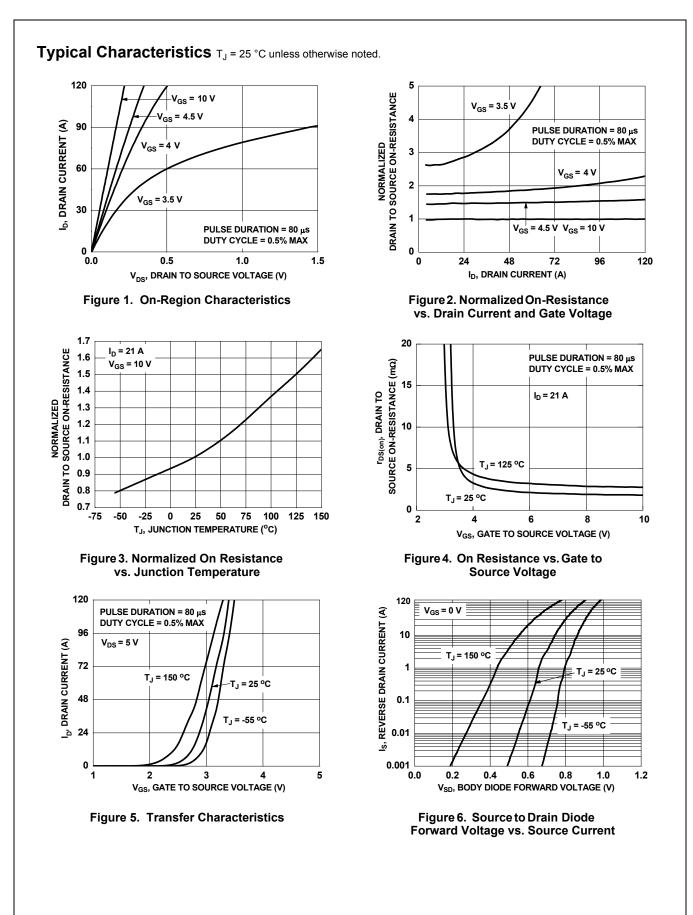
a. 60 °C/W when mounted on a 1 in² pad of 2 oz copper



b.160 °C/W when mounted on a minimum pad of 2 oz copper

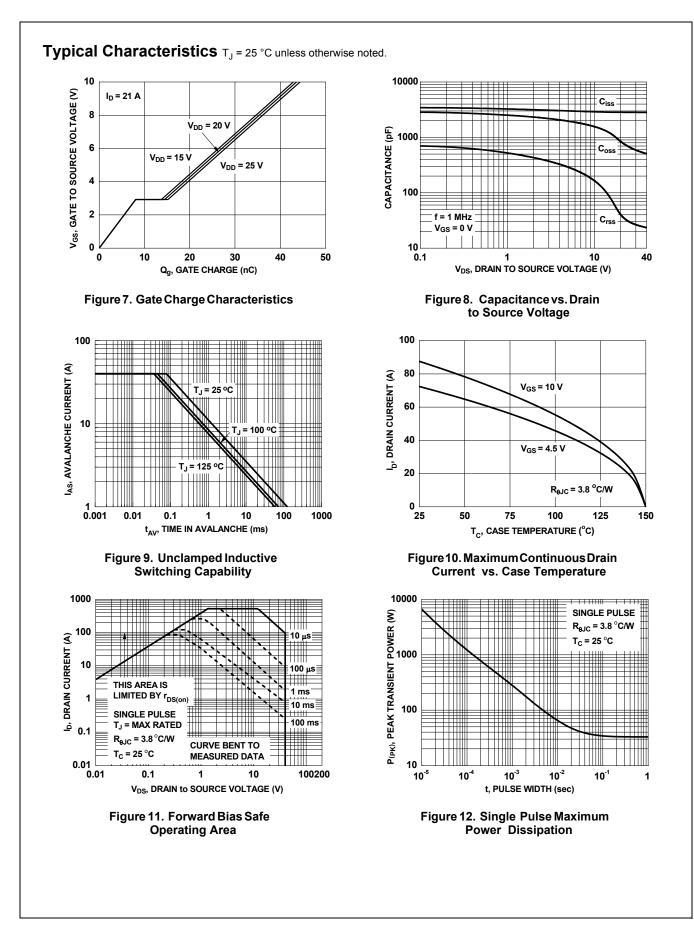
2. Pulse Test: Pulse Width < 300 $\mu s,$ Duty cycle < 2.0 %.

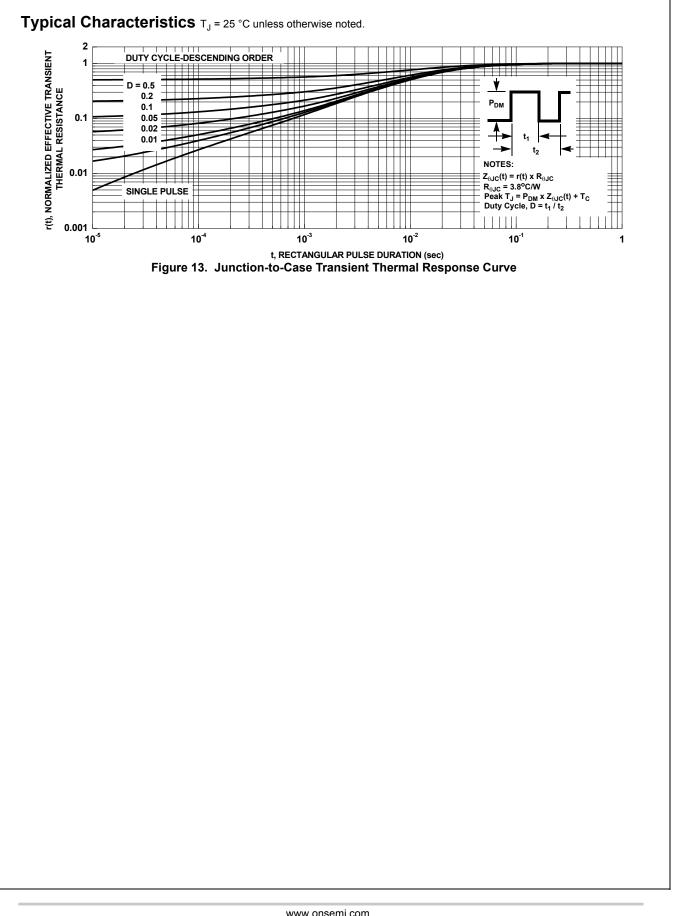
Pulse Test. Pulse within < 500 µs, Duty Cycle < 2.0 %.
E_{AS} of 216 mJ is based on starting T_J = 25 °C, L = 3 mH, I_{AS} = 12 A, V_{DD} = 40 V, V_{GS} = 10 V. 100% tested at L = 0.1 mH, I_{AS} = 40 A.
Pulse Id refers to Figure.11 Forward Bias Safe Operation Area.
Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

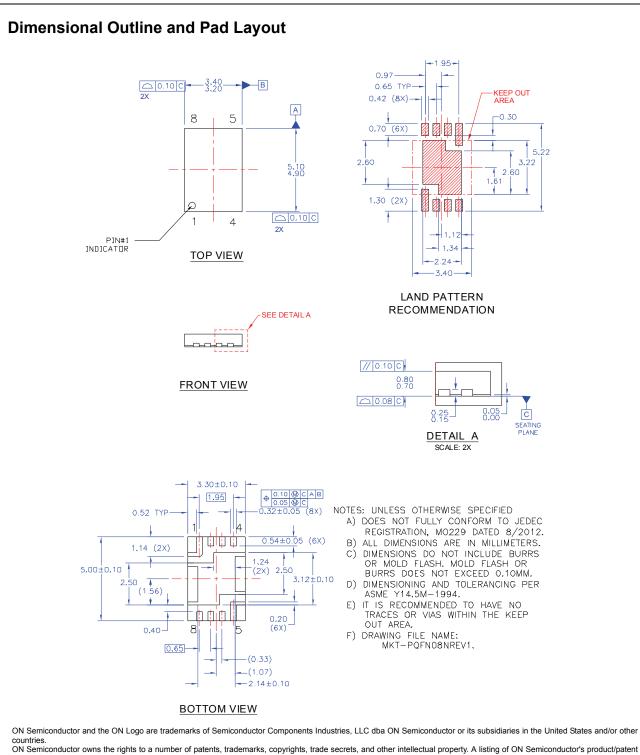


www.onsemi.com









ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or

standards, regardless of any support or applications information provided by ON Semiconductor. Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resal in any manner.

www.onsemi.com

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor has against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death ass

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC